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(54) **LEAKAGE REDUCTION IN OUTPUT DRIVER CIRCUITS**

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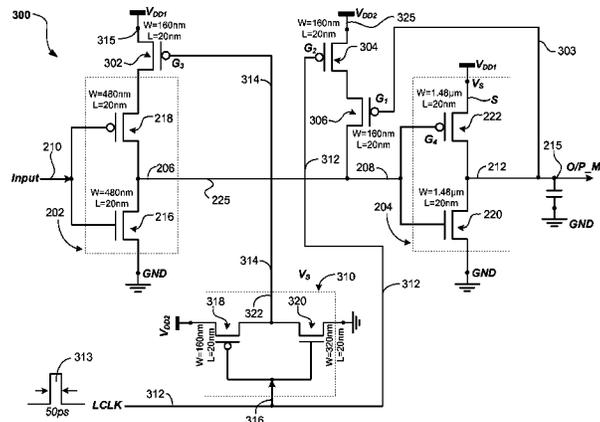
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(52) **U.S. Cl.**
CPC **H03K 19/0013** (2013.01); **H03K 19/0944** (2013.01); **H03K 19/0963** (2013.01); **H03K 5/135** (2013.01)

(57) **ABSTRACT**
An output driver circuit may include an electrically conductive medium, an output logic inverter having a first switch adapted to couple a first positive supply voltage to the electrically conductive medium and a second switch adapted to couple a ground supply voltage to the conductive medium. A first biasing network includes a first input that is coupled to the conductive medium, a second input that receives a clock signal, and a first output that is adapted to couple a second positive supply voltage to each input of the first and the second switch. Based on the second switch coupling the conductive medium to the ground supply voltage and the received clock signal generating a logic low, the biasing network reverse biases the first switch by coupling the second positive supply voltage to the respective input of the first switch causing a leakage current reduction in the first switch.

(58) **Field of Classification Search**
CPC H04L 25/0272; H04L 25/028; H04L 25/0292; H03K 19/0963; H03K 5/135; G06F 1/10
USPC 326/93, 95, 82, 83; 327/208-212, 214, 327/215; 365/203
See application file for complete search history.

15 Claims, 5 Drawing Sheets



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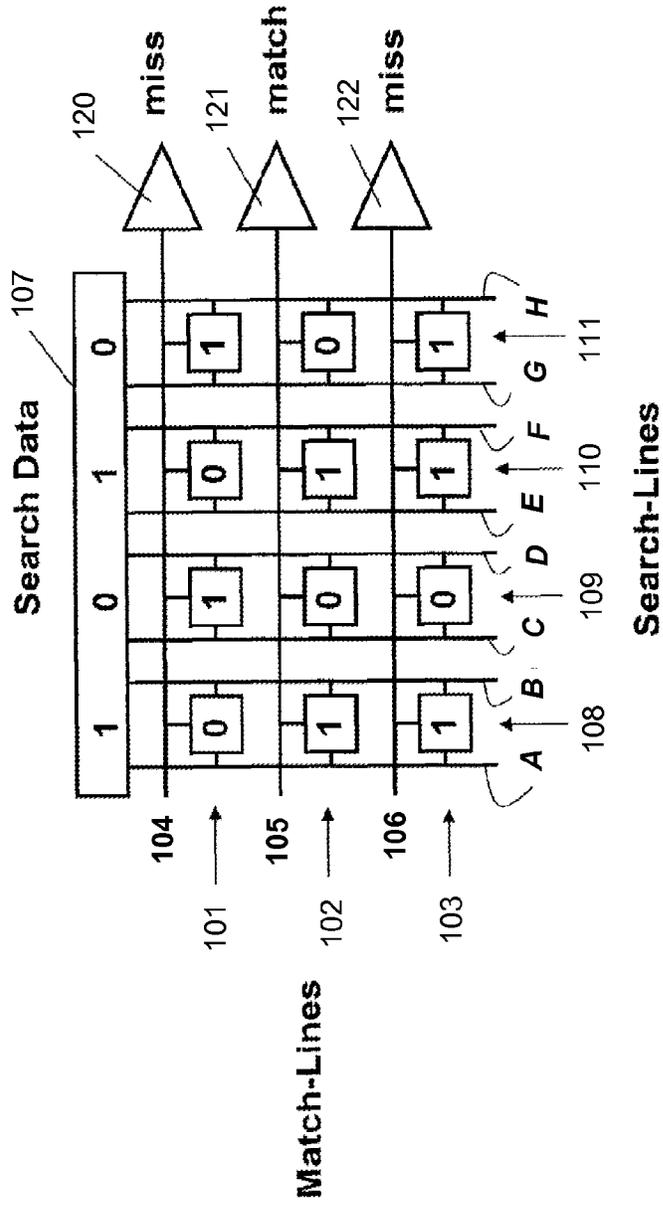


FIG. 1
(Prior Art)

120, 121, 122

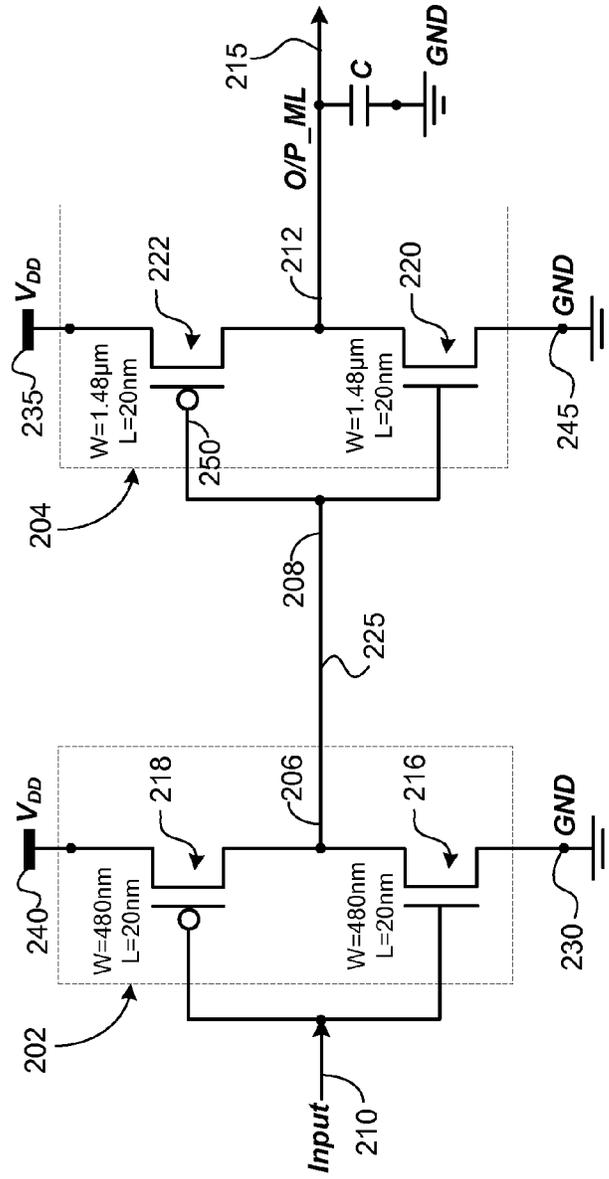


FIG. 2
(Prior Art)

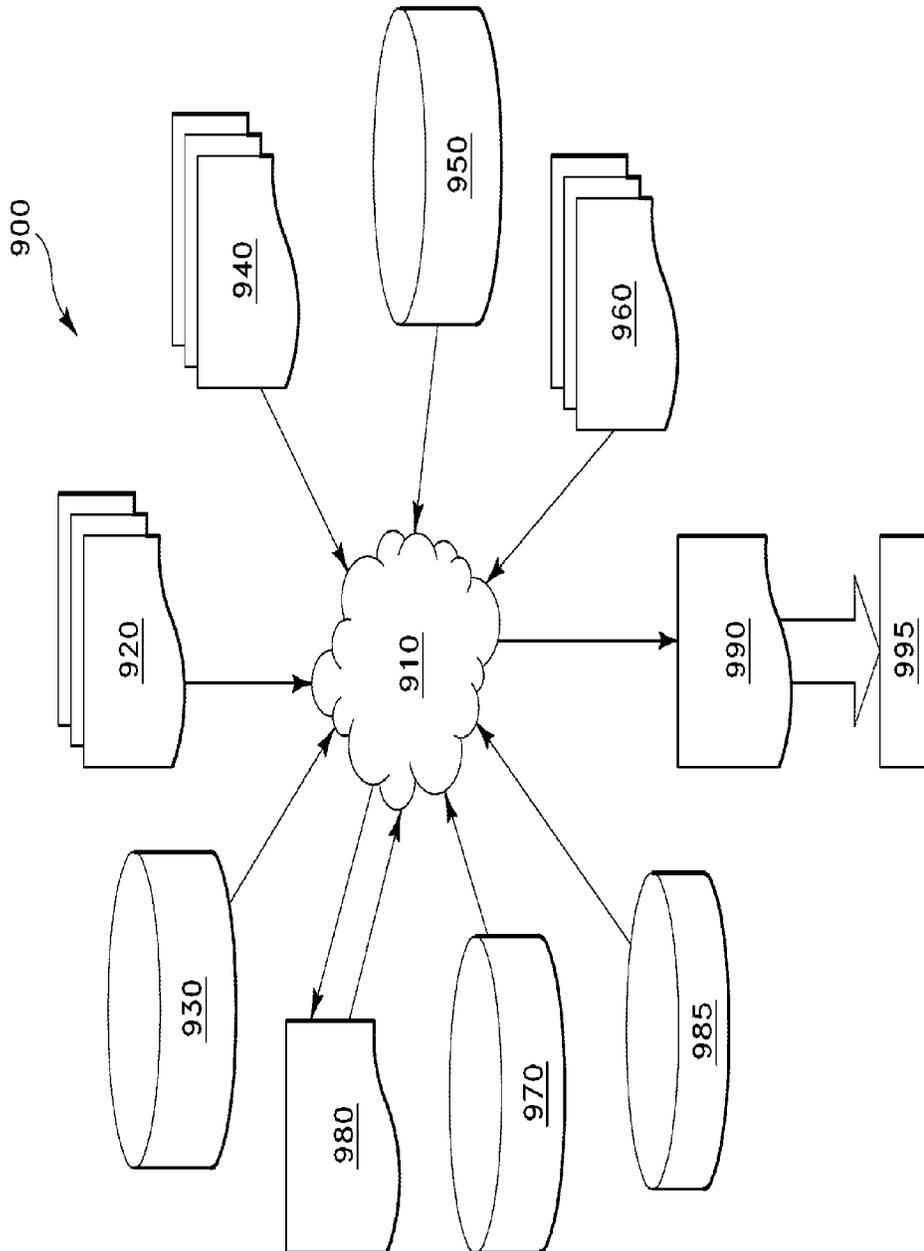


FIG. 5

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LEAKAGE REDUCTION IN OUTPUT DRIVER CIRCUITS

BACKGROUND

a. Field of the Invention

The present invention generally relates to output driver circuits, and more particularly, to reducing leakage in output driver circuits.

b. Background of Invention

An associative memory system such as Content Addressable Memory (CAM) may facilitate its memory cells to be referenced by their contents. Thus, CAM may be utilized in, for example, lookup table implementations, networking system applications, pattern recognition, and data compression. Among other things, CAMs provide the ability to perform a fast search operation in which search data is compared with data stored within the CAM. Typically search data is loaded onto search lines and compared with stored words in the CAM. During a search-and-compare operation, the CAM may perform a fully parallel search and generate a match or mismatch signal associated with each stored word, indicating whether the search word matches a stored word or not.

In order to allow this fast parallel comparison between all stored words to a single search word, each CAM word may contain dedicated search hardware. Each CAM cell, therefore, contains additional bit-comparison transistors, in addition to a conventional storage element, which may typically be implemented as a Static Random Access Memory (SRAM) cell or a Dynamic Random Access Memory (DRAM) cell. This added circuitry is combined across the word with a match-line (ML) to produce a match or mismatch signal for each CAM word. Moreover, this search hardware allows the entire contents of the CAM memory to be searched in a single memory cycle.

Since, leakage power minimization is becoming increasingly important as technology nodes progress, leakage power reduction in each component on a chip may also be of significance. One major contributor to CAM leakage may be matchline output drivers, which ultimately drive the search results. For example, a Ternary CAM (TCAM) system may include 8096 matchlines and, therefore, 8096 output drivers, which may contribute to current leakage and increased power consumption. Furthermore, most of the TCAM matchlines typically drive a miss state or GND causing leakage in the PFET drivers of their output drivers.

BRIEF SUMMARY

According to one exemplary embodiment, an output driver circuit may include a electrically conductive medium; an output logic inverter stage having a first switch adapted to couple a first positive supply voltage to the electrically conductive medium and a second switch adapted to couple a ground supply voltage to the electrically conductive medium; a first biasing network having a first input that is coupled to the electrically conductive medium, a second input that receives a clock signal, and a first output that is adapted to couple a second positive supply voltage to each respective input of the first and the second switch, such that the second positive supply voltage is greater than the first positive supply voltage. Based on the second switch coupling the electrically conductive medium to the ground supply voltage and the received clock signal generating a logic low, the biasing network reverse biases the first switch by coupling the second positive supply voltage to the respective input of the first switch causing a leakage current reduction in the first switch.

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According to another exemplary embodiment, a method of driving a electrically conductive medium using a logic inverter stage having a first and a second switch connected in series between a first positive supply voltage and a ground supply voltage is provided. The method may include applying a logic low to the electrically conductive medium using the first switch device; feeding back the logic low on the electrically conductive medium to an input of a third switch; applying a logic low clock signal to an input of a fourth switch; generating, using the third and the fourth switch, an electrical path between a second positive supply voltage and each respective input of the first and the second switch based on the applied logic low of the clock signal and the fed back logic low on the electrically conductive medium; and reverse biasing the second switch device by coupling the second positive supply voltage to the input of the second switch. The reverse bias may occur based on the first positive supply voltage and the second positive supply voltage being coupled to the second switch, whereby the reverse biased second switch causes a leakage current reduction in the second switch when the first switch applies the logic low to the electrically conductive medium.

According to yet another exemplary embodiment, a design structure tangibly embodied in a machine readable medium for designing, manufacturing, or testing an integrated circuit is provided. The design structure may include a electrically conductive medium; an output logic inverter stage having a first switch adapted to couple a first positive supply voltage to the electrically conductive medium and a second switch adapted to couple a ground supply voltage to the electrically conductive medium; a first biasing network having a first input that is coupled to the electrically conductive medium, a second input that receives a clock signal, and a first output that is adapted to couple a second positive supply voltage to each respective input of the first and the second switch, such that the second positive supply voltage being greater than the first positive supply voltage. Based on the second switch coupling the electrically conductive medium to the ground supply voltage and the received clock signal generating a logic low, the biasing network reverse biases the first switch by coupling the second positive supply voltage to the respective input of the first switch causing a leakage current reduction in the first switch.

BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWINGS

FIG. 1 illustrates an exemplary architecture for a conventional CAM arrangement;

FIG. 2 is a circuit diagram of a conventional inverter-based output driver;

FIG. 3 is a circuit diagram of an inverter-based output driver according to one embodiment;

FIG. 4 is a circuit diagram of an inverter-based output driver according to another embodiment; and

FIG. 5 is a flow diagram of a design process used in semiconductor design, manufacture, and/or test.

The drawings are not necessarily to scale. The drawings are merely schematic representations, not intended to portray specific parameters of the invention. The drawings are intended to depict only typical embodiments of the invention. In the drawings, like numbering represents like elements.

DETAILED DESCRIPTION

Referring to FIG. 1, in a conventional CAM sensing exemplary architecture **100**, CAM core cells may be arranged in

horizontal rows **101**, **102**, **103**, composed of, for example, four cells, whereby each of the CAM core cell of a respective horizontal row **101**, **102**, **103** are coupled to matchlines (MLs) **104**, **105**, **106**. For example, the CAM core cells of row **101** are coupled to ML **104**, the CAM core cells of row **102** are coupled to ML **105**, and the CAM core cells of row **103** are coupled to ML **106**. As depicted, for purposes of illustrative brevity, only a four-bit word associated with the horizontally arranged CAM core cells and three MLs **104-106** are shown. It may, however, be appreciated that any number of MLs and word lengths can be utilized.

As further depicted in FIG. 1, the CAM core cells are arranged in columns **108**, **109**, **110**, and **111**. While only four columns are shown, any number of columns corresponds to the number of bits (i.e., 4) in a CAM core cell word to be searched may be utilized. For example, '640' columns representative of a 640-bit word may be utilized. Search data **107** includes the word data to be searched and is provided for comparison with each word formed in CAM rows **101-103**. Although three CAM rows **101-103** are depicted, for example, '2000' CAM rows and, thus, '2000' MLs may be utilized. Parallel search lines A-H are coupled to search data **107**, and each CAM core cell in a respective column is coupled to two search lines so that each cell corresponding to a data bit of the search data **107** can be searched for a match. Search results develop on MLs **104-106** in parallel and are applied to respective output drivers **120-122**.

As indicated, a match may occur between search data **107** and the CAM core cell word coupled to ML **105**. Upon detection of such a match, output driver **121** may then transition to logic 1 (i.e., logic high), while the remaining output drivers **120**, **122** generate a logic 0. Thus, in operation, when a match is found, most of the output drivers coupled to the MLs will be in a logic 0 state, which in turn may contribute to leakage current generation. Such leakage current generation is described below in relation to a convention driver circuit depicted in FIG. 2.

Referring to FIG. 2, a conventional output driver, such as each of output drivers **120**, **121**, and **122** (also see FIG. 1), may include two inverter stages **202** and **204** coupled in series, whereby the output **206** of inverter stage **202** is coupled to the input **208** of inverter stage **204**. The depicted output driver includes two inverter stages **202**, **204** so that the logic level present at the input **210** to the output driver is the same as the logic level generated at the output **212** of the output driver. For example, a logic 0 at input **210** will generate a logic 0 at output **212**, while a logic 1 at input **210** will accordingly generate a logic 1 at output **212**.

Inverter stage **202** may include NFET device **216** and PFET device **218**. Also, inverter stage **204** may include NFET device **220** and PFET device **222**. In the depicted exemplary embodiment, inverter stage **204** may include wider FET devices **220**, **222**, as defined by W , compared to the FET devices **216**, **218** associated with inverter stage **202**. For example, FET devices **216** and **218** include a width W of about 480 nm, while FET devices **220** and **222** have widths W of about 1.48 μm . By increasing the device widths in the second inverter stage **204** (i.e., output logic inverter stage), the larger capacitive load C associated with the ML **215** can be driven by output **212**. However, by widening the FET devices, leakage current is also increased.

In operation, when a logic 1 is applied to input **210** of inverter stage **202** (i.e., input logic inverter stage), NFET **216** is switched on, while PFET **218** is switched off. The output **206** of inverter stage **202** and, therefore, the input **208** of inverter stage **204** is held at a logic 0 based on the NFET **216** coupling electrical connection **225** to ground GND, as indi-

cated at **230**. Since the input **208** of inverter stage **204** is held at a logic 0, the PFET **222** of inverter stage **204** is switch on, while NFET **220** is switched off. The output **212** of inverter stage **204** and, therefore ML line **215** is held at a logic 1 based on the PFET **222** coupling the supply voltage V_{DD} , as indicated at **235**, to ML line **215**.

Alternatively, when a logic 0 is applied to input **210** of inverter stage **202**, NFET **216** is switched off, while PFET **218** is switched on. The output **206** of inverter stage **202** and, therefore, the input **208** of inverter stage **204** is held at a logic 1 based on the PFET **218** coupling electrical connection **225** to the supply voltage V_{DD} , as indicated at **240**. Since the input **208** of inverter stage **204** is held at a logic 1, the NFET **220** of inverter stage **204** is switch on, while PFET **222** is switched off. The output **212** of inverter stage **204** and, therefore ML line **215** is held at a logic 0 based on the NFET **220** coupling the ML line **215** to ground GND, as indicated at **245**.

Although the ML line **215** is coupled to ground GND, some leakage current flow through the turned-off PFET **222** to output **212** and, therefore ML line **215**, may occur regardless of the input **250** of PFET **222** being turned off. In a typical CAM architecture, there may be, for example, '2000' MLs that each has an output driver such as output driver **120-122**. Due to the nature of the CAM function, many of the MLs (e.g., about 90%) in a CAM architecture may be held at logic 0 by their respective output drivers, based on the occurrence of a miss (i.e., no word match for that ML). Only a limited number of MLs may transition to logic 1 by their respective output driver, based on the occurrence of a word match (i.e., a word match found on the ML). Therefore, out of '2000' MLs, about 1800MLs (e.g., 90%) may be generating leakage current as their respective output drivers hold the ML lines at logic 0.

As previously described, PFET **222** may not be perfectly turned off when a logic 0 is received at input **210**. Particularly:

$$V_{GS} = V_G - V_S \quad (\text{Equation 1})$$

Using Equation 1, for PFET **222**, V_G is held at V_{DD} based on the output **206** of inverter stage **202** being held at logic 1. Also, V_S for PFET **222** is held at V_{DD} . Thus, V_{GS} is about 0V. Based on the PFET having a threshold voltage of V_p , the voltage input driving PFET **222** may be approximately $V_{GS} - V_p$, which is $0 - V_p = -V_p$. PFET **222** is accordingly turned off by $-V_p$. Although turned off, the PFET device **222** may still contribute to generating leakage current. The following one or more exemplary embodiments thus illustrate and describe feedback circuitry that may provide reverse biasing voltages across FET devices (e.g., PFET **222**) that drive electrical signal lines such as ML lines (e.g., ML **215**) for leakage reduction purposes.

FIG. 3 is a circuit diagram of an inverter-based output driver **300** according to one embodiment. As depicted, output driver **300** includes inverter stages **202** and **204**, which are identical to, or substantially the same as, the inverter stages depicted in FIG. 2. Output driver **300** further includes a PFET device **302** that is coupled between supply voltage V_{DD1} at **315** and PFET **218**; and a broken feedback circuit that includes feedback connection **303**, PFET **304**, and PFET **306**. As depicted, the feedback connection **303** is coupled to the gate G_1 of PFET **306**, while PFETs **304** and **306** are connected in series between supply voltage V_{DD2} at **325** and input **208** of the inverter stage **204**. The feedback connection **303** may be broken when PFET **304** is turned OFF during an update operation. Alternatively, the feedback connection **303** may be active when PFETs **304** and **306** are turned ON during a static (i.e., no update) operation. A more detailed description of the static and update functions associated with output driver **300**

is presented in the following paragraphs. The supply voltages V_{DD1} , V_{DD2} may include separate supply voltages whereby V_{DD2} is greater than V_{DD1} .

The output driver **300** also operates in conjunction with a clocking source **310**. The clocking source **310** may be shared among all output drivers and provides a clock signal **312** and an inverted (i.e., complementary) version of the clock signal **314** to the output drivers. The clock signal **312** is received by the input **316** of the clocking source **310**. Since the clocking source **310** is an inverter formed by PFET device **318** and NFET device **320**, the clock signal **312** received at the input **316** to the clocking source **310** is inverted at the output **322** of the clocking source **310** in order to generate the inverted (i.e., complementary) clock signal **314**. As depicted, the clock signal **312** at input **316** bypasses the clocking source **310** and is received by the gate G_2 of PFET **304**. The inverted (i.e., complementary) clock signal **314** generated at the output **322** of the clocking source **310** is received by the gate G_3 of PFET **302**. Thus, PFET **304** is driven by the clock signal **312** and PFET **302** is driven by the inverted clock signal **314**.

In operation, typically two modes may exist. A first mode of operation is an update which is activated upon each pulse period **313** of clock signal **312**. The pulse period **313** of clock signal **312** may, for example, be approximately 50 ps. The other mode is a static mode, which applies when the clock signal **312** is at logic 0 (i.e., a logic low or no pulse transition). Because the update mode occurs for a relatively short period, the leakage current associated with the MLs that are held at logic 0 may be considered of little consequence. Therefore, in update mode, the output driver **300** is configured to function as a two-stage inverter having inverters **202** and **204**, which operates as described above in relation to FIG. 2.

Thus, during an update, the 50 ps pulse generates a logic 1 at input **316** of the clocking source **310**. The clocking source **310** then generates a logic 0 at output **322**, which is coupled to gate G_3 of PFET **302**. The generated logic 0, which is representative of inverted clock signal **314**, switches PFET **302** ON and, therefore, couples supply voltage V_{DD1} to the source of PFET **218**. Since the logic 1 at input **316** of the clocking source **310** is also coupled to gate G_2 of PFET **304**, PFET **304** remains switched OFF.

Thus, in such an operating mode (i.e., update), the output driver **300** functions as a driver including inverters **202** and **204**, whereby no leakage minimization measures are incorporated. Specifically, if input **210** is at logic 1, ML line **215** is also held at logic 1 via PFET **222**. Here, leakage may be of little concern. Alternatively, when input **210** is at logic 0, ML line **215** is also held at logic 0 via NFET **220**. Here, leakage may occur through PFET **222**. However, such exhibited leakage occurs over the relatively short 50 ps pulse period **313** during the update.

Alternatively, during a static mode, the clock is at a logic low and generates a logic 0 at input **316** of the clocking source **310**. The clocking source **310** accordingly generates a logic 1 at output **322**, which is coupled to gate G_3 of PFET **302**. The generated logic 1, which is representative of inverted clock signal **314**, switches PFET **302** OFF and, therefore, isolates supply voltage V_{DD1} from the source of PFET **218**. Since the logic 0 at input **316** of the clocking source **310** is also coupled to gate G_2 of PFET **304**, PFET **304** is switched ON. If, during the previous update, the input **210** was at logic 0, the output **206** of inverter stage **202** remains at logic 1 and, therefore, the input **208** of inverter stage **204** is also at logic 1. Based on the input **208** of inverter stage **204** being at logic 1, the output **212** of inverter stage **204** and, therefore, ML **215** is accordingly at logic 0.

As previously described, this condition, whereby the output **212** of the inverter stage **204** is at logic 0 through NFET **220**, applies to a leakage current scenario via PFET **222**. However, in this operating mode (i.e., static) the broken feedback circuit, provided by feedback connection **303**, PFET **304**, and PFET **306**, generates a reverse bias condition across PFET **222**. Particularly, since the clock signal **312** is at logic 0 and is applied to gate G_2 of PFET **304**, PFET **304** is switched ON. Also, based on the logic 0 at output **212** of the inverter stage **204** being fed back via feedback connection **303** to gate G_1 of PFET **306**, PFET **306** is also switched ON. PFET devices **304** and **306** may form a switched biasing network that is controlled by both the output **212** of the driver **300**, and thus the ML's **215** logic state, and the input clock signal **312** to the driver **300**. When both PFET devices **304**, **306** are switched ON, the biasing network is accordingly switched ON. Thus, during this condition, the V_{DD2} supply voltage is coupled to input **208** of inverter stage **204**. Now, instead of the V_{DD1} supply voltage being coupled to input **208** of inverter stage **204** via a logic 1 output from inverter stage **202**, the increased supply voltage provided by V_{DD2} is coupled to input **208** and, therefore, gate G_4 of PFET **222** of inverter stage **204**. This accordingly causes a reverse bias across PFET **222**. Based on the application of the reverse bias across PFET **222**, the leakage current through the PFET **222** is thus reduced. Particularly, a reverse bias path is created between the V_{DD2} supply voltage and the gate G_4 of PFET **222** via PFETs **304** and **306**.

As previously described, under conventional operating conditions during, for example, an update, the output driver **300** is configured to function as a two-stage inverter having inverters **202** and **204**, which accordingly operate in the manner described above in relation to FIG. 2. Thus, referring back to Equation (1) above, the voltage input driving PFET **222** may be approximately $V_{GS}-V_T$ whereby $V_{GS}=V_G-V_S$. Here, V_G is now V_{DD2} while V_S is V_{DD1} . Therefore, $V_{GS}=V_{DD2}-V_{DD1}=+V$, where $+V$ is representative of a positive (+) voltage based on $V_{DD2}>V_{DD1}$. So, $V_{GS}-V_T$ is equivalent to $+V-V_T$. This means that a more positive voltage is now applied to the gate G_4 of PFET **222**, which provides the reverse bias voltage across the device **222**. This reverse bias is evident based on the voltage (i.e., V_{DD2}) applied to gate G_4 of PFET **222** being higher than the voltage (i.e., V_{DD1}) applied to the source (S) of PFET **222**. For a PFET, the more positive the applied gate voltage, the more reversed biased and switched OFF is the device. Conversely, zero or negative voltages applied to the PFET gate may forward bias and switch ON the device. Here, by switching a path and coupling a higher supply voltage V_{DD2} to the gate G_4 of PFET **222**, the PFET **222** is reverse biased even more (V_{GS} further positively increased), which in turn increasingly negates leakage current. Since most of the MLs (e.g., 90%) are held at logic 0 by their respective output driver, having an output driver such as output driver **300** enables a reduction in leakage current as a result of the reverse biasing of the PFET (e.g., PFET **222**) of the output logic inverter stage (e.g., inverter **204**).

FIG. 4 is a circuit diagram of an inverter-based output driver **400** according to another embodiment. As depicted, output driver **400** also includes inverter stages **202** and **204**, which are identical to, or substantially the same as, the inverter stages depicted in FIG. 2. Moreover, the inverter-based output driver **400** includes the same circuitry and operating principles as the inverter-based output driver **300** of FIG. 3 during the reverse biasing of the output stage PFET **222** when the corresponding ML **215** is held at logic 0. However, additionally, the inverter-based output driver **400** also facilitates leakage current minimization for the output stage

NFET 220 when the corresponding ML 215 is held at logic 1. This may offer a benefit when, for example, the output driver 400 is driving a bus architecture or other electrically conductive medium that has a reasonable number of bus lines held at logic 1.

As depicted, output driver 400 also includes inverter stages 202 and 204, which are identical to, or substantially the same as, the inverter stages depicted in FIG. 2. Output driver 400 also includes PFET device 302 that is coupled between supply voltage V_{DD1} at 315 and PFET 218; and a first broken feedback circuit that includes feedback connection 303, PFET 304, and PFET 306. As depicted, the feedback connection 303 is coupled to the gate G_1 of PFET 306, while PFETs 304 and 306 are connected in series between supply voltage V_{DD2} at 325 and input 208 of the inverter stage 204. The feedback connection 303 may be broken when PFET 304 is turned OFF during the update operation. Alternatively, the feedback connection 303 may be active when PFETs 304 and 306 are turned ON during the static (i.e., no update) operation.

Output driver 400 also includes a second broken feedback circuit that includes feedback connection 403, NFET 404, and NFET 406. As depicted, the feedback connection 403 is coupled to the gate G_5 of NFET 404, while NFETs 404 and 406 are connected in series between below ground voltage BGND 425 and input 208 of the inverter stage 204. The feedback connection 403 may be broken when NFET 406 is turned OFF during an update operation. Alternatively, the feedback connection 403 may be active when NFETs 404 and 406 are turned ON during a static (i.e., no update) operation. A more detailed description of the static and update functions associated with output driver 400 is presented in the following paragraphs. The supply voltages V_{DD1} , V_{DD2} may, as previously indicated, include separate supply voltages whereby V_{DD2} is greater than V_{DD1} . Also, BGND is held to be below (i.e., more negative) ground GND or 0V.

The output driver 400 also operates in conjunction with a clocking source 310. The clocking source 310 may be shared among all output drivers and provides a clock signal 312 and an inverted (i.e., complementary) version of the clock signal 314 to the output drivers. The clock signal 312 is received by the input 316 of the clocking source 310. Since the clocking source 310 is an inverter formed by PFET device 318 and NFET device 320, the clock signal 312 received at the input 316 to the clocking source 310 is inverted at the output 322 of the clocking source 310 in order to generate the inverted (i.e., complementary) clock signal 314. As depicted, the clock signal 312 at input 316 bypasses the clocking source 310 and is received by the gate G_2 of PFET 304 and the gate G_7 of NFET 402. The inverted (i.e., complementary) clock signal 314 generated at the output 322 of the clocking source 310 is received by the gate G_3 of PFET 302 and gate G_6 of NFET 406. Thus, PFET 304 and NFET 402 are driven by the clock signal 312, while PFET 302 and NFET 406 are driven by the inverted clock signal 314.

As previously indicated, in operation, typically two modes may exist, whereby the first mode of operation is the update which is activated upon each pulse period 313 of clock signal 312. The pulse period 313 of clock signal 312 may, for example, be approximately 50 ps. The other mode is the static mode, which applies when the clock signal 312 is at logic 0 (i.e., no pulse transition). Because the update mode occurs for a relatively short period, the leakage current associated with the MLs that are held at logic 0 may be considered of little consequence. Therefore, in update mode, the output driver 400 is configured to function as a two-stage inverter having inverters 202 and 204, which operate as described above in relation to FIG. 2.

Thus, during the update, the 50 ps pulse generates a logic 1 at input 316 of the clocking source 310. The clocking source 310 then generates a logic 0 at output 322, which is coupled to both gate G_3 of PFET 302 and gate G_6 of NFET 406. The generated logic 0, which is representative of inverted clock signal 314, switches PFET 302 ON and NFET 406 OFF. Thus, supply voltage V_{DD1} is coupled to the source of PFET 218 and the BGND ground voltage at 425 is isolated from the drain of NFET 404. Since the logic 1 at input 316 of the clocking source 310 is also coupled to gate G_2 of PFET 304 and gate G_7 of NFET 402, PFET 304 remains switched OFF while NFET 402 is switched ON.

Thus, in such an operating mode (i.e., update), the output driver 400 functions as a driver including inverters 202 and 204, whereby no leakage minimization measures are incorporated. Specifically, if input 210 is at logic 1, ML line 215 is also held at logic 1 via PFET 222. Here, leakage may be of little concern. Alternatively, when input 210 is at logic 0, ML line 215 is also held at logic 0 via NFET 220. Here, leakage may occur through PFET 222. However, such exhibited leakage occurs over the relatively short 50 ps pulse period 313 during the update.

Alternatively, during the static mode, the clock is at a logic low and generates a logic 0 at input 316 of the clocking source 310. The clocking source 310 accordingly generates a logic 1 at output 322, which is coupled to both gate G_3 of PFET 302 and gate G_6 of NFET 406. The generated logic 1, which is representative of inverted clock signal 314, switches PFET 302 OFF and NFET 406 ON. Thus, PFET 302 isolates supply voltage V_{DD1} from the source of PFET 218, while NFET 406 couples the drain of NFET 404 to BGND ground at 425.

Since the logic 0 at input 316 of the clocking source 310 is coupled to gate G_2 of PFET 304, PFET 304 is switched ON. If, during the previous update, the input 210 was at logic 0, the output 206 of inverter stage 202 remains at logic 1 and, therefore, the input 208 of inverter stage 204 is also at logic 1. Based on the input 208 of inverter stage 204 being at logic 1, the output 212 of inverter stage 204 and, therefore, ML 215 is accordingly at logic 0. The logic 0 at input 316 of the clocking source 310 is also coupled to gate G_7 of NFET 402. Thus, NFET 402 is switch OFF and isolates the ground voltage at 415 from the drain of NFET 216.

As previously described, this condition, whereby the output 212 of the inverter stage 204 is at logic 0 through NFET 220, applies to a leakage current scenario via PFET 222. However, in this operating mode (i.e., static) the broken feedback circuit, provided by feedback connection 303, PFET 304, and PFET 306, generates a reverse bias condition across PFET 222. Particularly, since the clock signal 312 is at logic 0 and is applied to gate G_2 of PFET 304, PFET 304 is switched ON. Also, based on the logic 0 at output 212 of the inverter stage 204 being fed back via feedback connection 303 to gate G_1 of PFET 306, PFET 306 is also switched ON. PFET devices 304 and 306 may form a biasing network that is controlled by both the output 212 of the driver 300, and thus the ML's 215 logic state, and the input clock signal 312 to the driver 300. When both PFET devices 304, 306 are switched ON, the biasing network is accordingly switched ON. Thus, during this condition, the V_{DD2} supply voltage is coupled to input 208 of inverter stage 204. Now, instead of the V_{DD1} supply voltage being coupled to input 208 of inverter stage 204, the increased supply voltage provided by V_{DD2} is coupled to input 208 and, therefore, gate G_4 of PFET 222 of inverter stage 204. This accordingly causes a reverse bias across PFET 222. Based on the reverse bias across PFET 222, the leakage current through the PFET 222 is accordingly reduced.

Further, based on the logic 0 at output **212** of the inverter stage **204** being fed back via feedback connection **403** to gate G_5 of NFET **404**, NFET **404** is switched OFF. Also, since the inverted version of the clock signal **314** is at logic 1 and is applied to gate G_6 of NFET **406**, NFET **406** is switched ON. However, the feedback connection is broken as a result of NFET **404** being OFF. Moreover, NFET devices **404** and **406** may form a switched biasing network that is controlled by both the output **212** of the driver **400**, and thus the ML's **215** logic state, and the output clock signal **314** from clocking source **310**.

When both NFET devices **404**, **406** are switched ON, the biasing network is accordingly switched ON and, therefore, input **208** and consequently the gate G_8 of NFET **220** is negatively biased by establishing an electrical connection between BGND **425** (i.e., below ground voltage) and gate G_8 of NFET **220** via conducting NFETs **404** and **408**. This negative biasing of the NFET **220** causes a reduction in leakage current when the NFET **220** is switched OFF based on output **212** being held at logic 1. More particularly, during the static operation, the inverted version of the clock signal **314** is at a logic 1 and received by the gate G_6 of NFET **406**. This causes NFET **406** to switch ON. If the output **212** of the inverter stage **204** (or driver output) and thus the ML **215** is also at logic 1, the positive voltage of this logic 1 at gate G_5 of NFET **404** causes the NFET **404** to switch ON. Therefore, a reverse bias path is created between BGND **425** and NFET **220** via NFETs **404** and **408**, which are both switched ON.

Thus, the embodiment of FIG. 4 provides leakage minimization during the static operating mode (i.e., clock **312** at logic 0) for instances where either PFET **222** is OFF (i.e., NFET **220** ON) or NFET **220** is OFF (i.e., PFET **222** ON). This provides additional leakage current minimization during instances (i.e., NFET **220** is OFF) when the ML **215** is held at logic 1 via PFET **222**. This may be advantageous for bus architectures that are held at logic 1 with more regularity than, for example, MLs that are mostly held at logic 0. In contrast, the embodiment of FIG. 3 provides leakage minimization during the static operating mode (i.e., clock **312** at logic 0) for instances where only PFET **222** is OFF (i.e., NFET **220** ON). This is, as previously discussed, due to the MLs mostly being held at logic 0 via NFET **220** while PFET **222** is OFF. In both embodiments, PFET **222** and NFET **220** include the output logic inverter stage **204** of output drivers **300** (FIG. 3) & **400** (FIG. 4). PFET **222** holds the output **212** and, therefore, ML **215** at logic 1, while NFET **220** holds the output **212** and, therefore, ML **215** at logic 0.

Although, the exemplary embodiments of FIGS. 3 & 4 are described in relation to CAM match-lines (ML), the output drivers **300** (FIG. 3) & **400** (FIG. 4) may be used to drive any electrically conductive medium such as, for example, data and/or address bus architectures, transmission lines, etc. Thus, the exemplary output driver **300** (FIG. 3), **400** (FIG. 4) embodiments facilitate a reduction in leakage current and overall device power consumption.

FIG. 5 shows a block diagram of an exemplary design flow **900** used for example, in semiconductor IC logic design, simulation, test, layout, and manufacture. Design flow **900** includes processes and mechanisms for processing design structures or devices to generate logically or otherwise functionally equivalent representations of the design structures and/or devices described above and shown in FIGS. 3 and 4. The design structure processed and/or generated by design flow **900** may be encoded on machine-readable transmission or storage media to include data and/or instructions that when executed or otherwise processed on a data processing system generate a logically, structurally, mechanically, or otherwise

functionally equivalent representation of hardware components, circuits, devices, or systems.

Design flow **900** may vary depending on the type of representation being designed. For example, a design flow **900** for building an application specific IC (ASIC) may differ from a design flow **900** for designing a standard component or from a design flow **900** for instantiating the design into a programmable array, for example a programmable gate array (PGA) or a field programmable gate array (FPGA) offered by Altera® Inc. or Xilinx® Inc.

FIG. 5 illustrates multiple such design structures including an input design structure **920** that is preferably processed by a design process **910**. In one embodiment, the design structure **920** comprises design data used in a design process and comprising information describing the embodiments of the invention with respect to the structures as shown in FIGS. 3 and 4. The design data in the form of schematics or HDL, a hardware-description language (e.g., Verilog, VHDL, C, etc.) may be embodied on one or more machine readable media. For example, design structure **920** may be a text file, numerical data or a graphical representation of the one or more embodiments of the invention shown in FIGS. 3 and 4. Design structure **920** may be a logical simulation design structure generated and processed by design process **910** to produce a logically equivalent functional representation of a hardware device. Design structure **920** may also or alternatively comprise data and/or program instructions that when processed by design process **910**, generate a functional representation of the physical structure of a hardware device. Whether representing functional and/or structural design features, design structure **920** may be generated using electronic computer-aided design (ECAD) such as implemented by a core developer/designer. When encoded on a machine-readable data transmission, gate array, or storage medium, design structure **920** may be accessed and processed by one or more hardware and/or software modules within design process **910** to simulate or otherwise functionally represent an electronic component, circuit, electronic or logic module, apparatus, device, or system such as that shown in FIGS. 3 and 4. As such, design structure **920** may comprise files or other data structures including human and/or machine-readable source code, compiled structures, and computer-executable code structures that when processed by a design or simulation data processing system, functionally simulate or otherwise represent circuits or other levels of hardware logic design. Such data structures may include hardware-description language (HDL) design entities or other data structures conforming to and/or compatible with lower-level HDL design languages such as Verilog and VHDL, and/or higher level design languages such as C or C++.

Design process **910** preferably employs and incorporates hardware and/or software modules for synthesizing, translating, or otherwise processing a design/simulation functional equivalent of the components, circuits, devices, or logic structure shown in FIGS. 3 and 4 to generate a netlist **980** which may contain a design structure such as design structure **920**. Netlist **980** may comprise, for example, compiled or otherwise processed data structures representing a list of wires, discrete components, logic gates, control circuits, I/O devices, models, etc. that describes the connections to other elements and circuits in an integrated circuit design. Netlist **980** may be synthesized using an iterative process in which netlist **980** is resynthesized one or more times depending on design specifications and parameters for the device. As with other design structure types described herein, netlist **980** may be recorded on a machine-readable data storage medium or programmed into a programmable gate array. The medium

may be a non-volatile storage medium such as a magnetic or optical disk drive, a programmable gate array, a compact flash, or other flash memory. Additionally, or in the alternative, the medium may be a system or cache memory, buffer space, or electrically or optically conductive devices and materials on which data packets may be transmitted and intermediately stored via the Internet, or other networking suitable means.

Design process **910** may include hardware and software modules for processing a variety of input data structure types including netlist **980**. Such data structure types may reside, for example, within library elements **930** and include a set of commonly used elements, circuits, and devices, including models, layouts, and symbolic representations, for a given manufacturing technology (e.g., different technology nodes, 20, 32 nm, 45 nm, 90 nm, etc.). The data structure types may further include design specifications **940**, characterization data **950**, verification data **960**, design rules **970**, and test data files **985** which may include input test patterns, output test results, and other testing information. Design process **910** may further include, for example, standard mechanical design processes such as stress analysis, thermal analysis, mechanical event simulation, process simulation for operations such as casting, molding, and die press forming, etc. One of ordinary skill in the art of mechanical design can appreciate the extent of possible mechanical design tools and applications used in design process **910** without deviating from the scope and spirit of the invention. Design process **910** may also include modules for performing standard circuit design processes such as timing analysis, verification, design rule checking, place and route operations, etc.

Design process **910** employs and incorporates logic and physical design tools such as HDL compilers and simulation model build tools to process design structure **920** together with some or all of the depicted supporting data structures along with any additional mechanical design or data (if applicable), to generate a second design structure **990** comprising second design data embodied on a storage medium in a data format used for the exchange of layout data of integrated circuits and/or symbolic data format (e.g. information stored in a GDSII (GDS2), GL1, OASIS, map files, or any other suitable format for storing such design structures). In one embodiment, the second design data resides on a storage medium or programmable gate array in a data format used for the exchange of data of mechanical devices and structures (e.g. information stored in an IGES, DXF, Parasolid XT, JT, DRG, or any other suitable format for storing or rendering such mechanical design structures). Similar to design structure **920**, design structure **990** preferably comprises one or more files, data structures, or other computer-encoded data or instructions that reside on transmission or data storage media and that when processed by an ECAD system generate a logically or otherwise functionally equivalent form of the embodiments of the invention shown in FIGS. **3** and **4**. In one embodiment, design structure **990** may comprise a compiled, executable HDL simulation model that functionally simulates the devices shown in FIGS. **3** and **4**.

Design structure **990** may also employ a data format used for the exchange of layout data of integrated circuits and/or symbolic data format (e.g. information stored in a GDSII (GDS2), GL1, OASIS, map files, or any other suitable format for storing such design data structures).

Design structure **990** may comprise information such as, for example, symbolic data, map files, test data files, design content files, manufacturing data, layout parameters, wires, levels of metal, vias, shapes, data for routing through the manufacturing line, and any other data required by a manu-

facturer or other designer/developer to produce devices or structures as described above and shown in FIGS. **3** and **4**. Design structure **990** may then proceed to a stage **995** where, for example, design structure **990**: proceeds to tape-out, is released to manufacturing, is released to a mask house, is sent to another design house, is sent back to the customer, etc.

The descriptions of the various embodiments of the present invention have been presented for purposes of illustration, but are not intended to be exhaustive or limited to the embodiments disclosed. Many modifications and variations will be apparent to those of ordinary skill in the art without departing from the scope and spirit of the described embodiments. The terminology used herein was chosen to best explain the principles of the one or more embodiment, the practical application or technical improvement over technologies found in the marketplace, or to enable others of ordinary skill in the art to understand the embodiments disclosed herein.

What is claimed is:

1. An output driver circuit comprising:
an electrically conductive medium;

an output logic inverter stage having a first switch adapted to couple a first positive supply voltage to the electrically conductive medium and a second switch adapted to couple a ground supply voltage to the electrically conductive medium;

a first biasing network having a first input that is coupled to the electrically conductive medium, a second input that receives a clock signal, and a first output that is adapted to couple a second positive supply voltage to each respective input of the first and the second switch, the second positive supply voltage being greater than the first positive supply voltage,

wherein, based on the second switch coupling the electrically conductive medium to the ground supply voltage and the received clock signal generating a logic low, the first biasing network reverse biases the first switch by coupling the second positive supply voltage to the respective input of the first switch causing a leakage current reduction in the first switch;

a clocking source that receives the clock signal and generates an inverted version of the clock signal, wherein the clocking source includes a logic inverter;

an input logic inverter stage coupled to the output logic inverter stage, the input logic inverter stage having a fifth switch adapted to couple the first positive supply voltage to the each respective input of the first and the second switch, and a sixth switch adapted to couple the ground supply voltage to the each respective input of the first and the second switch; and

a seventh switch coupled between the first positive supply voltage and the fifth switch, wherein the seventh switch receives the inverted version of the clock signal.

2. The circuit of claim **1**, wherein the first switch comprises a PFET device and the second switch comprises a NFET device.

3. The circuit of claim **2**, wherein the first biasing network comprises a third and a fourth switch connected in series between the second positive supply voltage and the each respective input of the first and the second switch, the third switch receiving the clock signal and the fourth switch being coupled to the electrically conductive medium.

4. The circuit of claim **3**, wherein the third and the fourth switch comprise PFET devices.

5. The circuit of claim **2**, wherein the electrically conductive medium comprises a match line associated with a content addressable memory (CAM) architecture.

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6. The circuit of claim 1, wherein the fifth switch comprises a PFET device and the sixth switch comprises a NFET device.

7. The circuit of claim 1, further comprising:

a second biasing network having a third input that is coupled to the electrically conductive medium, a fourth input that receives an inverted version of the clock signal, and a second output that is adapted to couple a below ground supply voltage to each respective input of the first and the second switch, the below ground supply voltage being less than the ground supply voltage.

8. The circuit of claim 7, wherein the second biasing network comprises a third and a fourth switch connected in series between the below ground supply voltage and the each respective input of the first and the second switch, the third switch receiving the inverted version of the clock signal and the fourth switch being coupled to the electrically conductive medium.

9. The circuit of claim 8, wherein the third and the fourth switch comprise NFET devices.

10. A method of driving an electrically conductive medium using a logic inverter stage having a first and a second switch connected in series between a first positive supply voltage and a ground supply voltage, the method comprising:

applying a logic low to the electrically conductive medium using the first switch device;

feeding back the logic low on the electrically conductive medium to an input of a third switch;

applying a logic low clock signal to an input of a fourth switch;

generating, using the third and the fourth switch, an electrical path between a second positive supply voltage and each respective input of the first and the second switch based on the applied logic low of the clock signal and the fed back logic low on the electrically conductive medium;

reverse biasing the second switch device by coupling the second positive supply voltage to the input of the second switch, the reverse bias occurring based on the first positive supply voltage and the second positive supply voltage being coupled to the second switch,

wherein the reverse biased second switch causes a leakage current reduction in the second switch when the first switch applies the logic low to the electrically conductive medium; applying a logic high to the electrically conductive medium using the second switch device;

feeding back the logic high on the electrically conductive medium to an input of a fifth switch;

applying a logic high inverted version of the clock signal to an input of a sixth switch;

generating, using the fifth and the sixth switch, an electrical path between a below ground supply voltage and each respective input of the first and the second switch based on the applied logic high of the inverted version of the clock signal and the fed back logic high on the electrically conductive medium; and

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reverse biasing the first switch device by coupling the below ground supply voltage to the input of the first switch, the reverse bias occurring based on the ground supply voltage and the below ground supply voltage being coupled to the first switch,

wherein the reverse biased first switch causes a leakage current reduction in the first switch when the second switch applies the logic high to the electrically conductive medium.

11. The method of claim 10, wherein the first switch comprises a NFET device and the second switch comprises a PFET device.

12. The method of claim 11, wherein the NFET device applies the logic low to the electrically conductive medium by coupling the electrically conductive medium to the ground supply voltage when the PFET device is switched OFF, and wherein the PFET device applies a logic high to the electrically conductive medium by coupling the electrically conductive medium to the first positive supply voltage when the NFET device is switched OFF.

13. The method of claim 10, wherein the second positive supply voltage is greater than the first positive supply voltage.

14. The method of claim 10, wherein the third and the fourth switches comprise PFET devices.

15. An output driver circuit comprising:

an electrically conductive medium;

an output logic inverter stage having a first switch adapted to couple a first positive supply voltage to the electrically conductive medium and a second switch adapted to couple a ground supply voltage to the electrically conductive medium;

a first biasing network having a first input that is coupled to the electrically conductive medium, a second input that receives a clock signal, and a first output that is adapted to couple a second positive supply voltage to each respective input of the first and the second switch, the second positive supply voltage being greater than the first positive supply voltage,

wherein, based on the second switch coupling the electrically conductive medium to the ground supply voltage and the received clock signal generating a logic low, the biasing network reverse biases the first switch by coupling the second positive supply voltage to the respective input of the first switch causing a leakage current reduction in the first switch; and

a second biasing network having a third input that is coupled to the electrically conductive medium, a fourth input that receives the inverted version of the clock signal, and a second output that is adapted to couple a below ground supply voltage to each respective input of the first and the second switch, the below ground supply voltage being less than the ground supply voltage.

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